

54F/74F373 Octal Transparent Latch with TRI-STATE® Outputs

General Description

The 'F373 consists of eight latches with TRI-STATE outputs for bus organized system applications. The flip-flops appear transparent to the data when Latch Enable (LE) is HIGH. When LE is LOW, the data that meets the setup times is latched. Data appears on the bus when the Output Enable (\overline{OE}) is LOW. When \overline{OE} is HIGH the bus output is in the high impedance state.

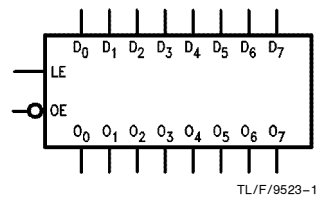
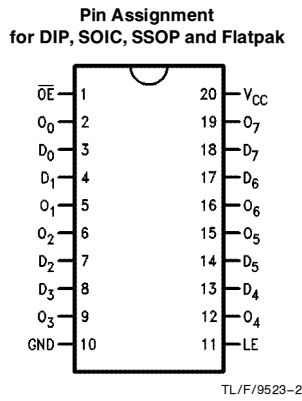
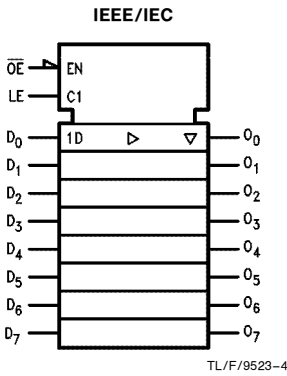
Features

- Eight latches in a single package
- TRI-STATE outputs for bus interfacing
- Guaranteed 4000V minimum ESD protection

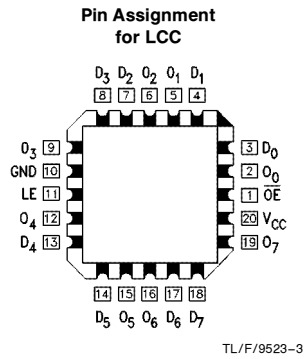
Commercial	Military	Package Number	Package Description
74F373PC		N20A	20-Lead (0.300" Wide) Molded Dual-In-Line
	54F373DM (QB)	J20A	20-Lead Ceramic Dual-In-Line
74F373SC (Note 1)		M20B	20-Lead (0.300" Wide) Molded Small Outline, JEDEC
74F373SJ (Note 1)		M20D	20-Lead (0.300" Wide) Molded Small Outline, EIAJ
74F373MSA (Note 1)		MSA20	20-Lead Molded Shrink Small Outline, EIAJ Type II
	54F373FM (QB)	W20A	20-Lead Cerpack
	54F373LM (QB)	E20A	20-Lead Ceramic Leadless Chip Carrier, Type C

Note 1: Devices also available in 13" reel. Use suffix = SCX, SJX, and MSAX.

Logic Symbols



Connection Diagrams



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Unit Loading/Fan Out

Pin Names	Description	54F/74F	
		U.L. HIGH/LOW	Input I_{IH}/I_{IL} Output I_{OH}/I_{OL}
D ₀ -D ₇	Data Inputs	1.0/1.0	20 μ A / -0.6 mA
LE	Latch Enable Input (Active HIGH)	1.0/1.0	20 μ A / -0.6 mA
\overline{OE}	Output Enable Input (Active LOW)	1.0/1.0	20 μ A / -0.6 mA
O ₀ -O ₇	TRI-STATE Latch Outputs	150/40 (33.3)	-3 mA / 24 mA (20 mA)

Functional Description

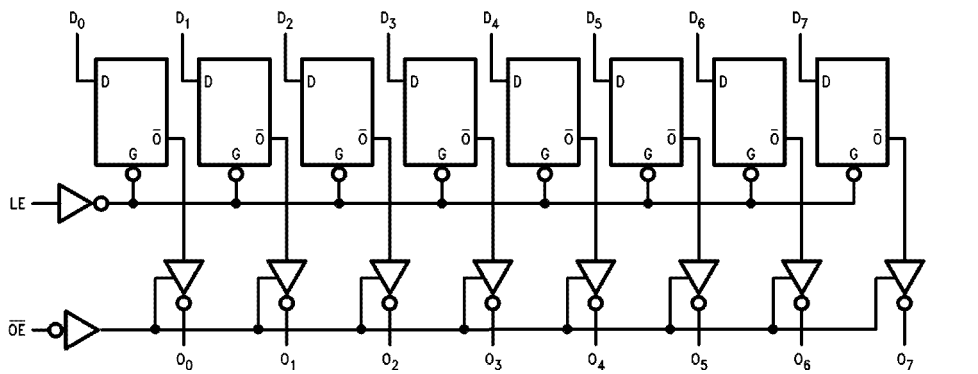
The 'F373 contains eight D-type latches with TRI-STATE output buffers. When the Latch Enable (LE) input is HIGH, data on the D_n inputs enters the latches. In this condition the latches are transparent, i.e., a latch output will change state each time its D input changes. When LE is LOW, the latches store the information that was present on the D inputs a setup time preceding the HIGH-to-LOW transition of LE. The TRI-STATE buffers are controlled by the Output Enable (\overline{OE}) input. When \overline{OE} is LOW, the buffers are in the bi-state mode. When \overline{OE} is HIGH the buffers are in the high impedance mode but this does not interfere with entering new data into the latches.

Truth Table

Inputs			Output
LE	\overline{OE}	D _n	O _n
H	L	H	H
H	L	L	L
L	L	X	O _n (no change)
X	H	X	Z

H = HIGH Voltage Level
 L = LOW Voltage Level
 X = Immaterial
 Z = High Impedance State

Logic Diagram



Please note that this diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.

TL/F/9523-5

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature	-65°C to +150°C
Ambient Temperature under Bias	-55°C to +125°C
Junction Temperature under Bias	-55°C to +175°C
Plastic	-55°C to +150°C
V _{CC} Pin Potential to Ground Pin	-0.5V to +7.0V
Input Voltage (Note 2)	-0.5V to +7.0V
Input Current (Note 2)	-30 mA to +5.0 mA

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

Voltage Applied to Output in HIGH State (with V _{CC} = 0V)	-0.5V to V _{CC}
Standard Output	-0.5V to +5.5V
TRI-STATE Output	-0.5V to +5.5V
Current Applied to Output in LOW State (Max)	twice the rated I _{OL} (mA)
ESD Last Passing Voltage (Min)	4000V

Recommended Operating Conditions

Free Air Ambient Temperature	-55°C to +125°C
Military	0°C to +70°C
Commercial	
Supply Voltage	+4.5V to +5.5V
Military	+4.5V to +5.5V
Commercial	

DC Electrical Characteristics

Symbol	Parameter	54F/74F			Units	V _{CC}	Conditions
		Min	Typ	Max			
V _{IH}	Input HIGH Voltage	2.0			V		Recognized as a HIGH Signal
V _{IL}	Input LOW Voltage			0.8	V		Recognized as a LOW Signal
V _{CD}	Input Clamp Diode Voltage			-1.2	V	Min	I _{IN} = -18 mA
V _{OH}	Output HIGH Voltage	54F 10% V _{CC} 54F 10% V _{CC} 74F 10% V _{CC} 74F 10% V _{CC} 74F 5% V _{CC} 74F 5% V _{CC}	2.5 2.4 2.5 2.4 2.7 2.7		V	Min	I _{OH} = -1 mA I _{OH} = -3 mA I _{OH} = -1 mA I _{OH} = -3 mA I _{OH} = -1 mA I _{OH} = -3 mA
V _{OL}	Output LOW Voltage	54F 10% V _{CC} 74F 10% V _{CC}		0.5 0.5	V	Min	I _{OL} = 20 mA I _{OL} = 24 mA
I _{IH}	Input HIGH Current	54F 74F		20.0 5.0	μA	Max	V _{IN} = 2.7V
I _{BVI}	Input HIGH Current Breakdown Test	54F 74F		100 7.0	μA	Max	V _{IN} = 7.0V
I _{CEX}	Output HIGH Leakage Current	54F 74F		250 50	μA	Max	V _{OUT} = V _{CC}
I _{ID}	Input Leakage Test	74F	4.75		V	0.0	I _{ID} = 1.9 μA All Other Pins Grounded
I _{OD}	Output Leakage Circuit Current	74F		3.75	μA	0.0	V _{IOD} = 150 mV All Other Pins Grounded
I _{IL}	Input LOW Current			-0.6	mA	Max	V _{IN} = 0.5V
I _{OZH}	Output Leakage Current			50	μA	Max	V _{OUT} = 2.7V
I _{OZL}	Output Leakage Current			-50	μA	Max	V _{OUT} = 0.5V
I _{OS}	Output Short-Circuit Current			-60	mA	Max	V _{OUT} = 0V
I _{ZZ}	Bus Drainage Test			500	μA	0.0V	V _{OUT} = 5.25V
I _{CCZ}	Power Supply Current		38	55	mA	Max	V _O = HIGH Z

AC Electrical Characteristics

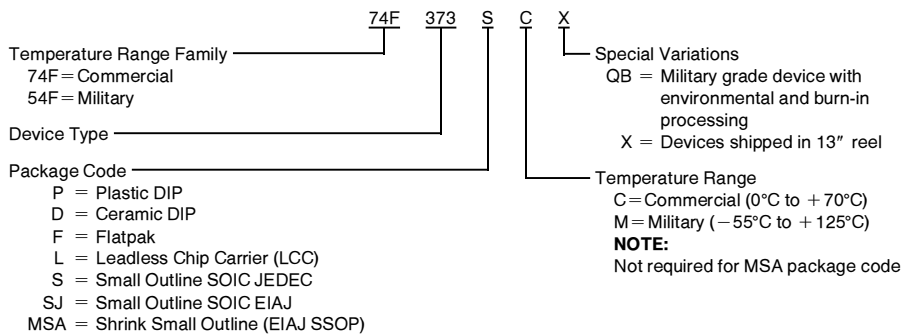
Symbol	Parameter	74F			54F		74F		Units
		T _A = +25°C V _{CC} = +5.0V C _L = 50 pF			T _A , V _{CC} = Mil C _L = 50 pF		T _A , V _{CC} = Com C _L = 50 pF		
		Min	Typ	Max	Min	Max	Min	Max	
t _{PLH} t _{PHL}	Propagation Delay D _n to O _n	3.0 2.0	5.3 3.7	7.0 5.0	3.0 2.0	8.5 7.0	3.0 2.0	8.0 6.0	ns
t _{PLH} t _{PHL}	Propagation Delay LE to O _n	5.0 3.0	9.0 5.2	11.5 7.0	5.0 3.0	15.0 8.5	5.0 3.0	13.0 8.0	ns
t _{PZH} t _{PZL}	Output Enable Time	2.0 2.0	5.0 5.6	11.0 7.5	2.0 2.0	13.5 10.0	2.0 2.0	12.0 8.5	ns
t _{PHZ} t _{PLZ}	Output Disable Time	1.5 1.5	4.5 3.8	6.5 5.0	1.5 1.5	10.0 7.0	1.5 1.5	7.5 6.0	ns

AC Operating Requirements

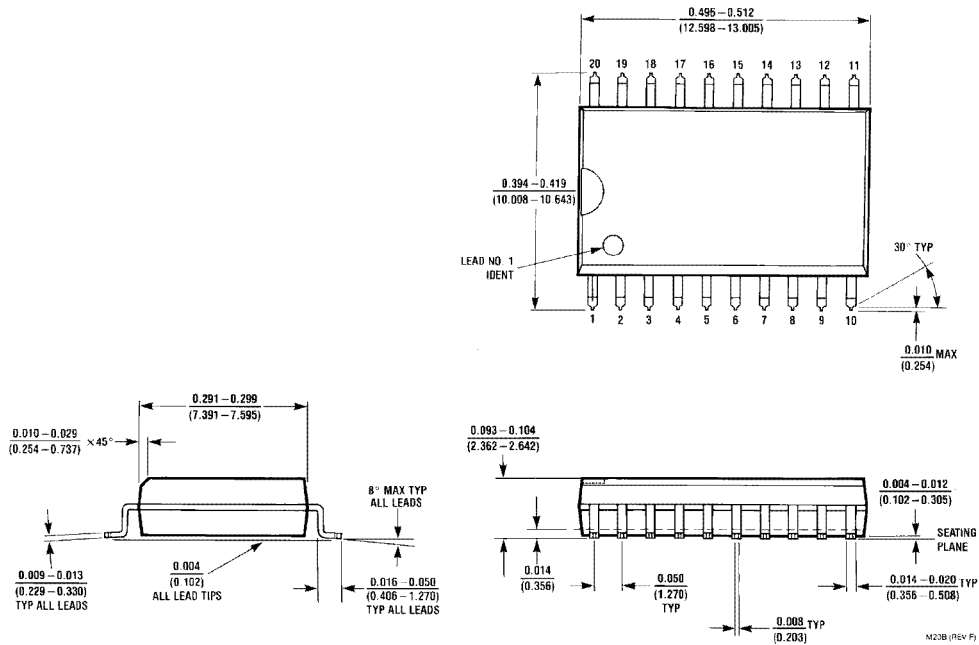
Symbol	Parameter	74F		54F		74F		Units
		T _A = +25°C V _{CC} = +5.0V		T _A , V _{CC} = Mil		T _A , V _{CC} = Com		
		Min	Max	Min	Max	Min	Max	
t _s (H) t _s (L)	Setup Time, HIGH or LOW D _n to LE	2.0		2.0		2.0		ns
t _h (H) t _h (L)	Hold Time, HIGH or LOW D _n to LE	3.0		3.0	4.0	3.0		
t _w (H)	LE Pulse Width, HIGH	6.0		6.0		6.0		ns

Ordering Information

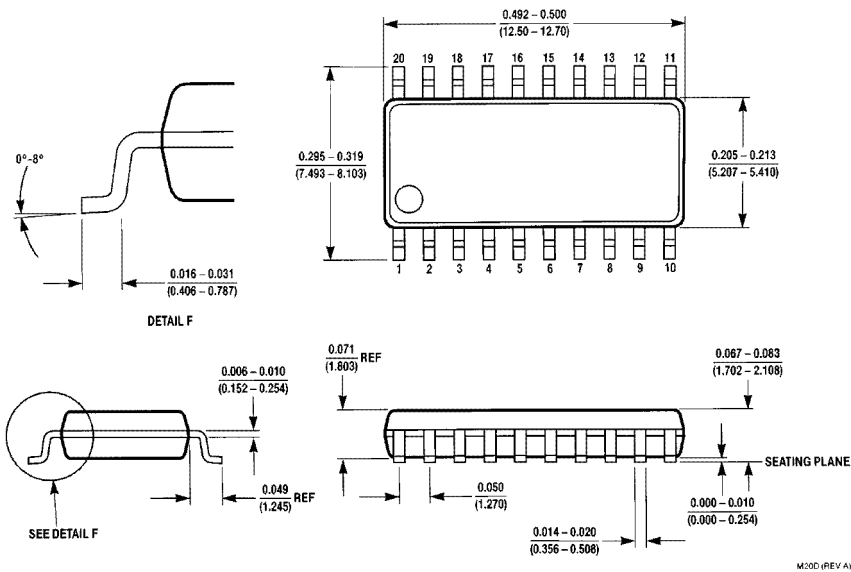
The device number is used to form part of a simplified purchasing code where the package type and temperature range are defined as follows:



Physical Dimensions inches (millimeters) (Continued)

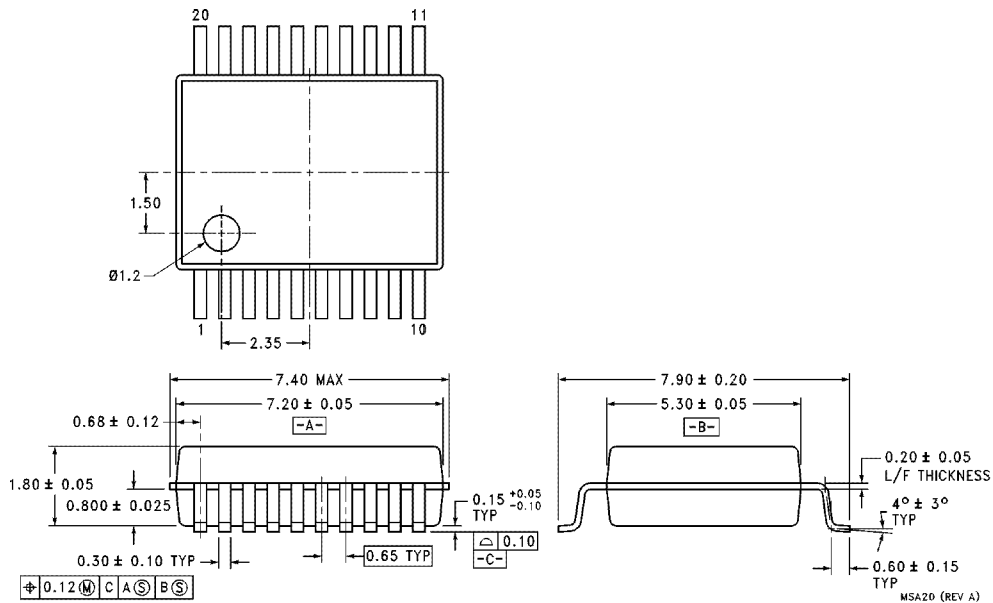


**20-Lead (0.300" Wide) Molded Small Outline Package, JEDEC (S)
NS Package Number M20B**

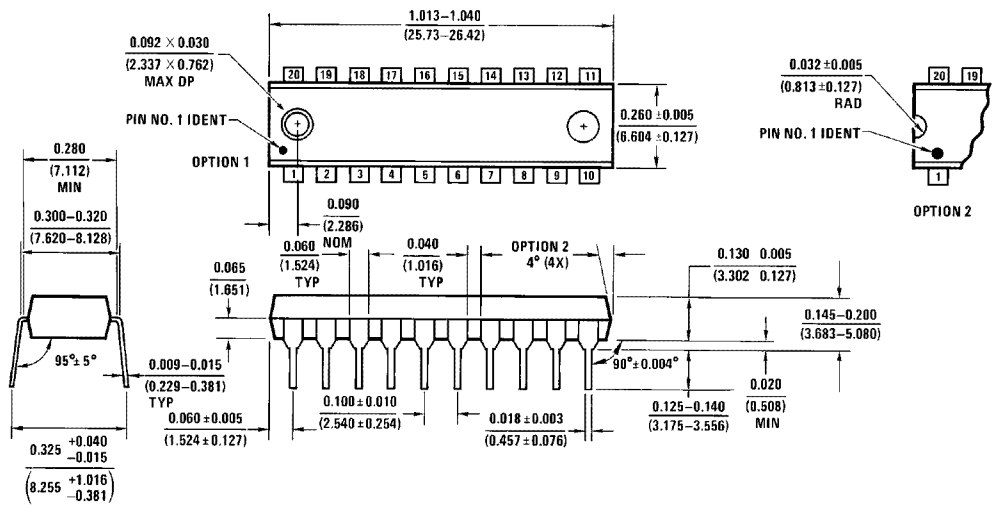


**20-Lead (0.300" Wide) Small Outline Package, EIAJ (SJ)
NS Package Number M20D**

Physical Dimensions inches (millimeters) (Continued)

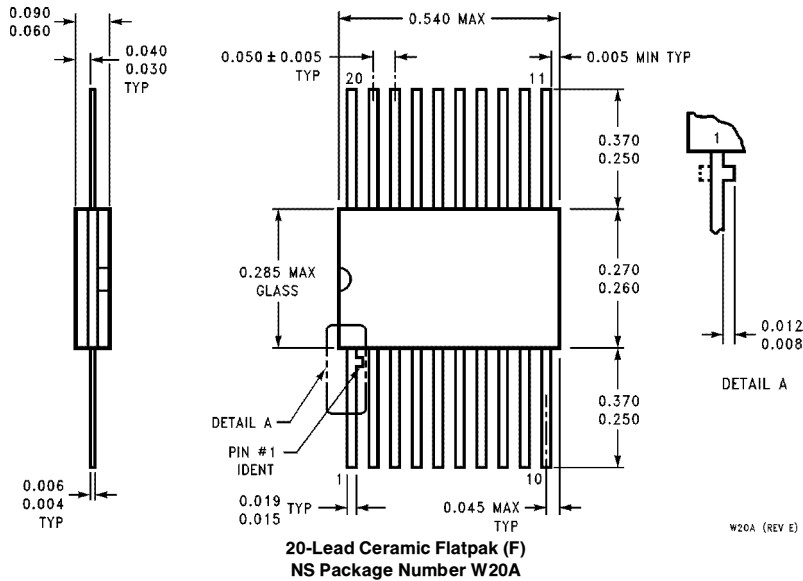


20-Lead Molded Shrink Small Outline Package, EIAJ, Type II (MSA)
NS Package Number MSA20



20-Lead (0.300" Wide) Molded Dual-In-Line Package (P)
NS Package Number N20A

Physical Dimensions inches (millimeters) (Continued)



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National Semiconductor Corporation
2900 Semiconductor Drive
P.O. Box 58090
Santa Clara, CA 95052-8090
Tel: 1(800) 272-9959
TWX: (910) 339-9240

National Semiconductor GmbH
Livry-Gargan-Str. 10
D-82256 Fürstenfeldbruck
Germany
Tel: (61-41) 35-0
Telex: 527649
Fax: (61-41) 35-1

National Semiconductor Japan Ltd.
Sumitomo Chemical
Engineering Center
Bldg. 7F
1-7-1, Nakase, Mihama-Ku
Chiba-City,
Chiba Prefecture 261
Tel: (043) 299-2300
Fax: (043) 299-2500

National Semiconductor Hong Kong Ltd.
13th Floor, Straight Block,
Ocean Centre, 5 Canton Rd.
Tsimshatsui, Kowloon
Hong Kong
Tel: (852) 2737-1600
Fax: (852) 2736-9960

National Semicondutores Do Brazil Ltda.
Rue Deputado Lacorda Franco
120-3A
Sao Paulo-SP
Brazil 05418-000
Tel: (55-11) 212-5066
Telex: 391-1131931 NSBR BR
Fax: (55-11) 212-1181

National Semiconductor (Australia) Pty, Ltd.
Building 16
Business Park Drive
Monash Business Park
Nottingham, Melbourne
Victoria 3168 Australia
Tel: (3) 558-9999
Fax: (3) 558-9998

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